

# **BCR5AS-12B**

## Triac

Medium Power Use

(The product guaranteed maximum junction temperature of 150°C)

REJ03G0451-0300 Rev.3.00 Nov 30, 2007

### **Features**

• I<sub>FGT I</sub>, I<sub>RGT I</sub>, I<sub>RGT III</sub>: 30 mA

Non-Insulated Type

Planar Passivation Type

### **Outline**

RENESAS Package code: PRSS0004ZA-A (Package name: MP-3A)





- 1. T<sub>1</sub> Terminal
- 2. T<sub>2</sub> Terminal
- 3. Gate Terminal
- 4. T<sub>2</sub> Terminal

### **Applications**

Hybrid IC, solid state relay, switching mode power supply, light dimmer, electric fan, electric blanket, control of household equipment such as washing machine, and other general purpose control applications

### Warning

- 1. Refer to the recommended circuit values around the triac before using.
- 2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Farameter	Syllibol	12	Offic	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V	

### BCR5AS-12B (The product guaranteed maximum junction temperature of 150°C)

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T(RMS)</sub>	5	А	Commercial frequency, sine full wave 360° conduction, Tc = 128°C <sup>Note3</sup>
Surge on-state current	I <sub>TSM</sub>	50	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	10.4	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	3	W	
Average gate power dissipation	$P_{G(AV)}$	0.3	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	I <sub>GM</sub>	0.3	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	0.26	g	Typical value

Notes: 1. Gate open.

### **Electrical Characteristics**

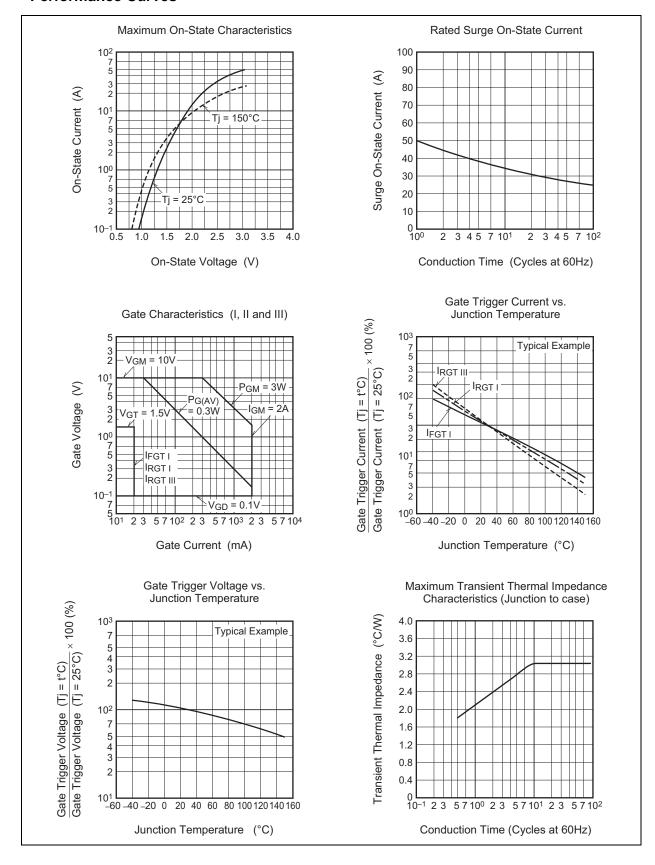
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 150°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.8	V	Tc = 25°C, I <sub>TM</sub> = 7 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT\ I}$	_	_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V <sub>RGT I</sub>	_	_	1.5	V	$R_G = 330 \Omega$
	III	V <sub>RGT III</sub>	_	_	1.5	V	
Gate trigger current <sup>Note2</sup>	I	I <sub>FGT I</sub>	_	_	30	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ $\Omega$ ,
	II	I <sub>RGT I</sub>	_	_	30	mA	$R_G = 330 \Omega$
	III	I <sub>RGT III</sub>	_	_	30	mA	
Gate non-trigger voltage		$V_{GD}$	0.2/0.1	_	_	V	Tj = 125°C/150°C,
							$V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th(j-c)</sub>	_	_	3.0	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	5/1	_	_	V/µs	Tj = 125°C/150°C

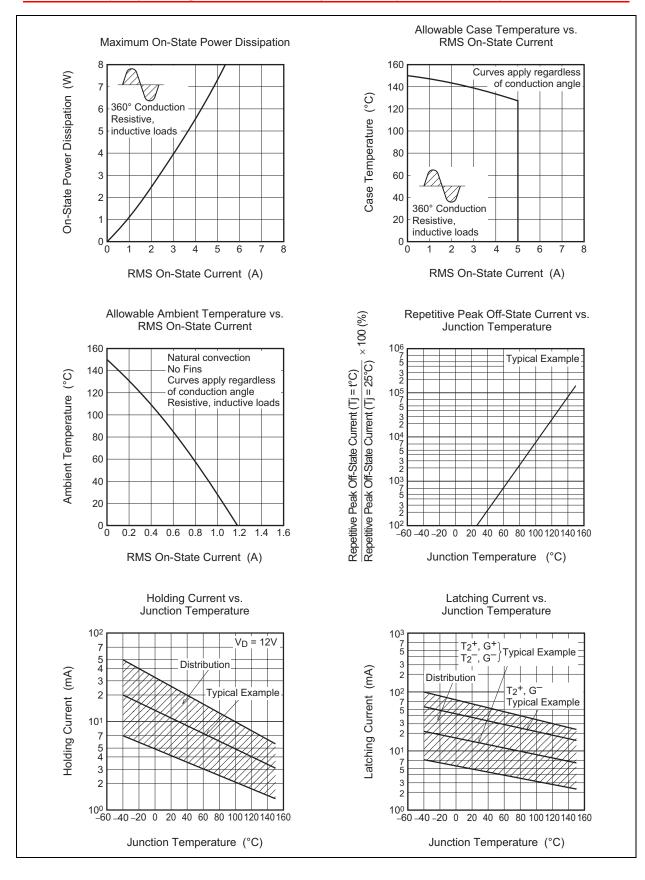
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

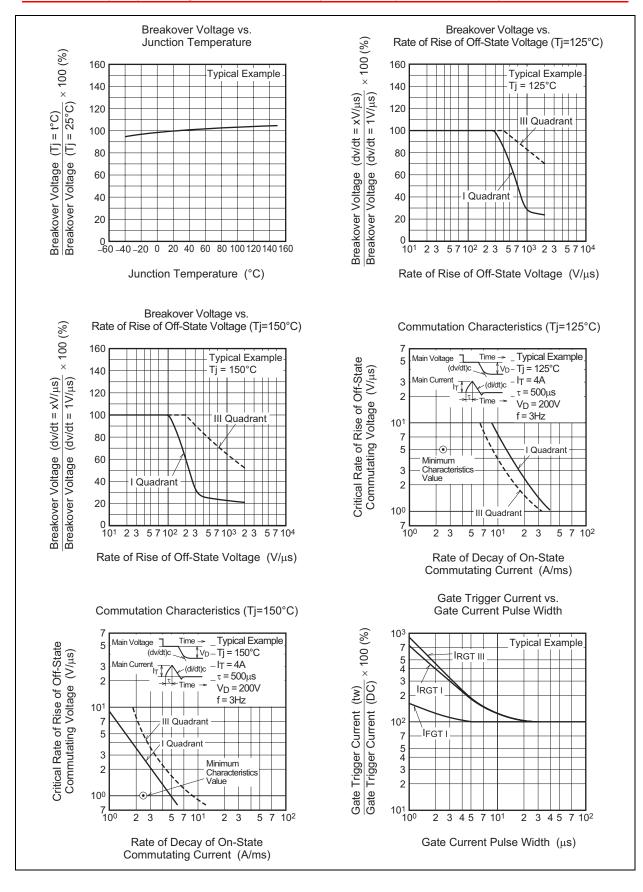
- 3. Case temperature is measured on the  $T_2$  tab.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

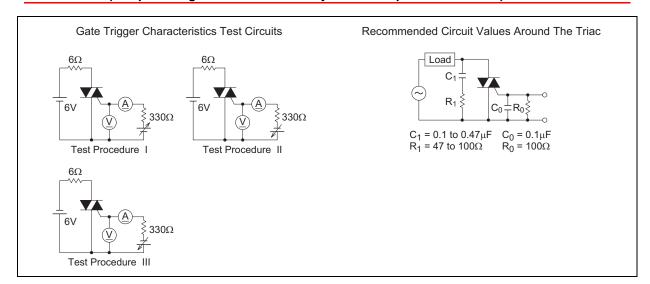
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage  → Time
2. Rate of decay of on-state commutating current (di/dt)c = -2.5 A/ms 3. Peak off-state voltage V <sub>D</sub> = 400 V	Main Current  Main Voltage  (dv/dt)c  Time  (dv/dt)c

### **Performance Curves**

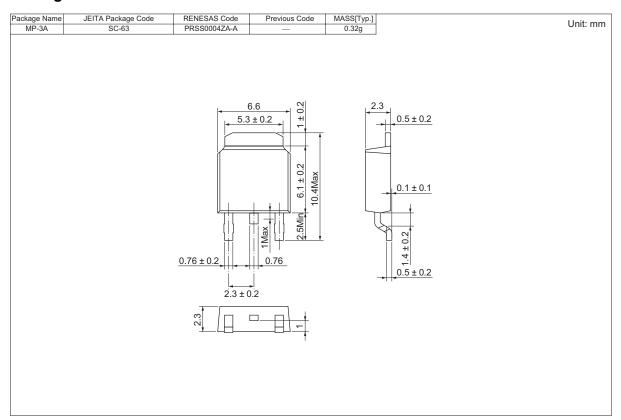








### **Package Dimensions**



### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	BCR5AS-12B-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	BCR5AS-12B

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

  Notes:

  1. This document is provided for reference purposes only so that Penesas customers may select the appropriate Renesas products for their use. Renesas neither makes in the respect to the accuracy or completeness of the information contained in this document nor grants any license to any intellectual property rights or any other rights of Renesas or any third party with respect to the information in this document.

  2. Renesas shall have no liability for damages or infringement of any intellectual property or other rights arising out of the use of any information in this document, including, but not limited to, product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products or the technology described in this document for the purpose of military applications such as the development of waspons of mass and included in this document such as product data, diagrams, and regulations, and procedures required by such law and regulations and procedures required by such law and regulations and procedures required by such law and regulations, and procedures required by such law and regulations and procedures required by such law and regulations and procedures required by such law and regulations and procedures required by such law and regulations, and procedures required to such as a few such as a s



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510